## $Mn^{2+}-V_{Zn}$ charge transfer complexes in $Zn_{1-x}Mn_xTe$

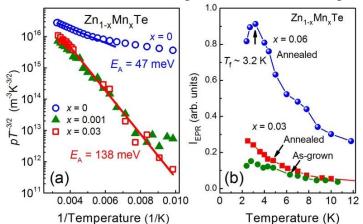
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 $Zn_{1-x}Mn_x$ Te dilute magnetic semiconductor (DMS) has recently attracted much attention due to the possibility of creation of the Mn-Mn ferromagnetic coupling [1] and fabrication of highly spin polarized red-green light emitting devices [2]. It is commonly believed that in  $II_{1-x}Mn_x$ VI DMSs  $Mn^{2+}$  ions are electrically neutral. Recently, we have reported that in  $Zn_{1-x}Mn_x$ Te doped with phosphorus (P) the  $Mn^{2+}$  ions strongly couple with P-acceptors giving rise to the compensation of the P-acceptors and the creation of  $Mn^{3+}$  ions [3].

In this communication, we report the results of the Hall effect, photoluminescence (PL), magneto-PL and electron paramagnetic resonance measurements performed on the undoped

ZnTe and Zn<sub>1-x</sub>Mn<sub>x</sub>Te crystals, which show a strong interaction between Mn<sup>2+</sup> ions and singly negatively charged zinc vacancy defects  $V_{Zn}^{-}$  resulting in the formation of the Mn<sup>2+</sup>- $V_{Zn}^{-}$  charge transfer complexes. The Mn<sup>2+</sup>- $V_{Zn}^{-}$  charge transfer complexes. The Mn<sup>2+</sup>- $V_{Zn}^{-}$  charge transfer complexes. The Mn<sup>2+</sup>- $V_{Zn}^{-}$  charge transfer complexes the transformation of the 0.047 eV  $V_{Zn}^{-/0}$  shallow acceptor level, present in ZnTe, into a 0.138 eV  $V_{Zn}^{-/-}$  deep acceptor level [see Fig. (a)]. This points to



a 0.138 eV  $V_{Zn}^{--/-}$  deep acceptor level [see Fig. (a)]. This points to the compensation of the  $V_{Zn}^{-/0}$  shallow acceptor level by Mn<sup>2+</sup> ions. We have suggested a charge transfer mechanism which transforms the Mn<sup>2+</sup>- $V_{Zn}^{-}$  complexes into Mn<sup>3+</sup>- $V_{Zn}^{--}$  ones,

$$Mn^{2+}(3d^{5},4s^{2}) + V_{Zn}^{-} \to Mn^{2+}(3d^{5},4s^{1}) + V_{Zn}^{--} \to Mn^{3+}(3d^{4},4s^{2}) + V_{Zn}^{--}.$$

The PL spectra measured under the 2.21 eV excitation for  $Zn_{0.96}Mn_{0.04}$ Te sample exhibit two PL bands locating at 1.96 eV and 1.44 eV, which are attributed to the intrashell transitions of  $Mn^{2+}$  and  $Mn^{3+}$  ions, respectively.

The coexistence of the mixed valence  $Mn^{2+}$  and  $Mn^{3+}$  states leads to local ferromagnetic (FM) double exchange interaction between  $Mn^{2+}$  and  $Mn^{3+}$  ions by the Zener double exchange mechanism. The competition between the  $Mn^{2+}-Mn^{3+}$  FM double exchange interaction and the intrinsic  $Mn^{2+}-Mn^{2+}$  antiferromagnetic superexchange coupling gives rise to the paramagnetic–spin glass phase transition at  $T_f = 3.2$  K in  $Zn_{0.94}Mn_{0.06}$ Te sample [see Fig. (b)].

We have observed that the compensation of the acceptor impurities or cation vacancy defects by  $Mn^{2+}$  ions is the inherent property not only for  $II_{1-x}Mn_xVI$  DMSs but also for  $III_{1-x}Mn_xV$  alloys. This finding calls for a new strategy for the efficient *p*-type doping of the Mn-based DMSs.

[1] Le Van Khoi, A. Avdonin, and A. Mycielski, *Phys. Rev. B* 107, 085206 (2023).

[2] Le Van Khoi and R. R. Gałązka, Appl. Phys. Lett. 98, 112103 (2011).

[3] Le Van Khoi, W. Dobrowolski, T. Kazimierczuk, A. Rodek, P. Kossacki, R.R. Galazka, and W. Zawadzki, *Phys. Rev. B* 101, 054440 (2020).